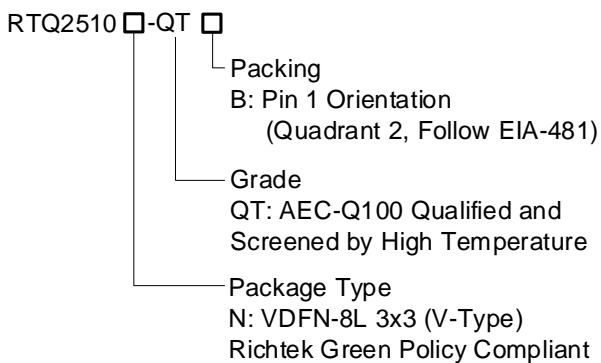


1A, Low Noise, High PSRR, Low-Dropout Linear Regulator

1 General Description

The RTQ2510 is a high performance positive low dropout (LDO) regulator designed for applications requiring very low dropout voltage and high Power Supply Ripple Rejection (PSRR) at up to 1A. The input voltage range is from 2.2V to 6V and the output voltage is programmable as low as 0.8V. The P-MOSFET switch provides excellent transient response with only a 4.7μF ceramic output capacitor. The external enable control effectively reduces power dissipation while shutdown and further output noise immunity is achieved through bypass capacitor on NR pin. Additionally, the RTQ2510 features a precise 3% output regulation over line, load, and temperature variations. The device is available in the VDFN-8L 3x3 package and is specified from -40°C to 125°C.

2 Ordering Information



Note:

Richtek products are Richtek Green Policy compliant and compatible with the current requirements of IPC/JEDEC J-STD-020

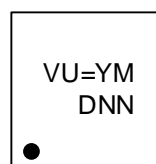
3 Features

- AEC-Q100 Grade 1 Qualified
- Dropout : 170mV Typical at 1A
- PSRR : 63dB @ 1kHz, 38dB @ 1MHz
- Input Voltage Range : 2.2V to 6V
- Adjustable Output Voltage : 0.8V to 5.5V
- -40°C to 125°C Operating Junction Temperature Range
- Excellent Noise Immunity
- Fast Response Over Load and Line Transient
- Stable with a 4.7μF Output Ceramic Capacitor
- Accurate Output Voltage 3% Over Load, Line, Process, and Temperature Variations
- Enable Control
- Over-Current Protection
- Over-Temperature Protection

4 Applications

- In-Vehicle Infotainment Systems
- Telematics Control Units
- Instrument Clusters
- Automotive Head Units
- ADAS Camera and Radar
- Navigation Systems

5 Marking Information



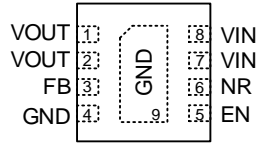
VU= : Product Code
YMDNN : Date Code

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6 Pin Configuration

(TOP VIEW)

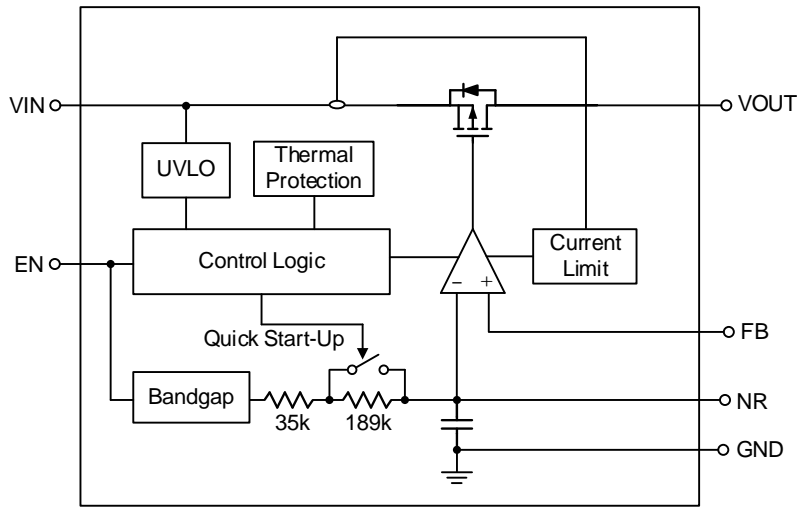


VDFN-8L 3x3

7 Functional Pin Description

Pin No.	Pin Name	Pin Function
1, 2	VOUT	Output of the regulator. Decouple this pin to GND with at least 4.7 μ F for stability.
3	FB	Feedback voltage input. This pin is used to set the desired output voltage via an external resistive divider. The feedback reference voltage is 0.8V typically.
4, 9 (Exposed Pad)	GND	System ground. The exposed pad must be soldered to a large PCB and connected to GND for maximum power dissipation.
5	EN	Enable control input. Connecting this pin to logic high enables the regulator or driving this pin low puts it into shutdown mode. EN can be connected to IN if not used. (EN pin is not allowed to be left floating.)
6	NR	Noise reduction input. Decouple this pin to GND with an external capacitor can not only reduce output noise to very low levels but also slow down the VOUT rise like a soft-start behavior.
7, 8	VIN	Supply input. A minimum of 1 μ F ceramic capacitor should be placed as close as possible to this pin for better noise rejection.

8 Functional Block Diagram



9 Absolute Maximum Ratings

(Note 1)

- All Pins ----- -0.3V to 7V
- Lead Temperature (Soldering, 10 sec.) ----- 260°C
- Junction Temperature ----- 150°C
- Storage Temperature Range ----- -65°C to 150°C

Note 1. Stresses beyond those listed under “Absolute Maximum Ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions may affect device reliability.

10 ESD Ratings

(Note 2)

- ESD Susceptibility
- HBM (Human Body Model)----- 2kV

Note 2. Devices are ESD sensitive. Handling precautions are recommended.

11 Recommended Operating Conditions

(Note 3)

- Supply Input Voltage, VIN ----- 2.2V to 6V
- Junction Temperature Range----- -40°C to 125°C

Note 3. The device is not guaranteed to function outside its operating conditions.

12 Thermal Information

(Note 4 and Note 5)

Thermal Parameter		VDFN-8L 3x3	Unit
θ_{JA}	Junction-to-ambient thermal resistance (JEDEC standard)	60.82	°C/W
$\theta_{JC(Top)}$	Junction-to-case (top) thermal resistance	83.76	°C/W
$\theta_{JC(Bottom)}$	Junction-to-case (bottom) thermal resistance	10.48	°C/W
$\theta_{JA(EVB)}$	Junction-to-ambient thermal resistance (specific EVB)	45.06	°C/W
$\Psi_{JC(Top)}$	Junction-to-top characterization parameter	5.42	°C/W
Ψ_{JB}	Junction-to-board characterization parameter	26.17	°C/W

Note 4. For more information about thermal parameter, see the Application and Definition of Thermal Resistances report, [AN061](#).

Note 5. $\theta_{JA(EVB)}$, $\Psi_{JC(Top)}$ and Ψ_{JB} are measured on a high effective-thermal-conductivity four-layer test board which is in size of 70mm x 50mm; furthermore, all layers with 1 oz. Cu. Thermal resistance/parameter values may vary depending on the PCB material, layout, and test environmental conditions.

13 Electrical Characteristics

($V_{IN} = V_{OUT} + 0.5V$ or $2.2V$, $V_{OUT} = 0.8V$ and $5.5V$, $I_{OUT} = 1mA$, $V_{EN} = 2.2V$, $C_{NR} = 10nF$, $C_{OUT} = 4.7\mu F$, $T_J = -40^{\circ}C$ to $125^{\circ}C$, unless otherwise specified)

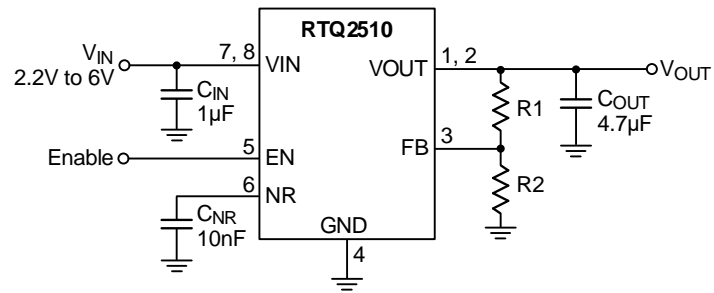
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit	
Supply Voltage							
VIN Supply Input Voltage	V_{IN}		2.2	--	6	V	
Undervoltage Lockout Rising Threshold	V_{UVLO}	$R_{OUT} = 1k\Omega$	1.86	2	2.1		
Undervoltage Lockout Hysteresis	V_{UVLO_HYS}	$R_{OUT} = 1k\Omega$	--	200	--	mV	
Shutdown Current	I_{SHDN}	$V_{EN} \leq 0.4V$, $V_{IN} \geq 2.2V$, $R_{OUT} = 1k\Omega$, $0^{\circ}C \leq T_J \leq 85^{\circ}C$	--	0.2	2	μA	
		$V_{EN} \leq 0.4V$, $V_{IN} \geq 2.2V$, $R_{OUT} = 1k\Omega$, $-40^{\circ}C \leq T_J \leq 125^{\circ}C$	--	0.2	5		
Quiescent Current	I_Q		--	190	350	μA	
Output Voltage							
Output Voltage	V_{OUT}		0.8	--	5.5	V	
Output Voltage Accuracy (Note 6)	V_{OUT_ACC}	$V_{OUT} + 0.5V \leq V_{IN} \leq 6V$, $V_{IN} \geq 2.5V$, $100mA \leq I_{OUT} \leq 500mA$, $0^{\circ}C \leq T_J \leq 85^{\circ}C$	-2	--	+2	%	
		$V_{OUT} + 0.5V \leq V_{IN} \leq 6V$, $V_{IN} \geq 2.2V$, $100mA \leq I_{OUT} \leq 1A$	-3	± 0.3	+3		
Line Regulation	V_{LINE_REG}	$V_{OUT} + 0.5V \leq V_{IN} \leq 6V$, $V_{IN} \geq 2.2V$, $I_{OUT} = 100mA$	--	0.2	--	%	
Load Regulation	V_{LOAD_REG}	$100mA \leq I_{OUT} \leq 1A$	--	0.3	--	%	
Enable Voltage							
EN Input Voltage Rising threshold	V_{EN_R}	V_{EN} rising, $2.2V \leq V_{IN} \leq 6V$, $R_{OUT} = 1k\Omega$	1.2	--	--	V	
EN Input Voltage Falling threshold	V_{EN_F}	V_{EN} falling, $R_{OUT} = 1k\Omega$	--	--	0.4		
EN Input Current	I_{EN}	$V_{IN} = 6V$, $V_{EN} = 6V$	--	0.02	1	μA	
FB Input Current	I_{FB}	$V_{IN} = 5.5V$, $V_{FB} = 0.8V$	--	0.02	1	μA	
Current Limit							
Current Limit	I_{LIM}	$V_{IN} = 3.3V$, $V_{OUT} = 0.85 \times V_{OUT}$	1.1	1.4	2	A	
Power-Up Time							
Soft-Start Time	tss	$V_{OUT} = 3.3V$, $R_{OUT} = 3.3k\Omega$, $C_{OUT} = 4.7\mu F$	$C_{NR} = 1nF$	--	0.16	--	ms
			$C_{NR} = 10nF$	--	1.6	--	

Dropout Voltage							
Dropout Voltage	V _{DROP}	V _{OUT} + 0.5V ≤ V _{IN} ≤ 6V, V _{FB} = 0V	V _{IN} ≥ 2.2V, I _{OUT} = 500mA	--	--	160	mV
			V _{IN} ≥ 2.5V, I _{OUT} = 750mA	--	--	210	
			V _{IN} ≥ 2.5V, I _{OUT} = 1A	--	--	370	
Power Supply Ripple Rejection and Noise							
Power Supply Ripple Rejection	PSRR	V _{IN} = 4.3V, V _{OUT} = 3.3V, I _{OUT} = 750mA (Note 7)	f = 100Hz	--	48	--	dB
			f = 1kHz	--	63	--	
			f = 10kHz	--	63	--	
			f = 1MHz	--	38	--	
Output Noise	V _n	BW = 100Hz to 100kHz, V _{IN} = 4.3V, V _{OUT} = 3.3V, I _{OUT} = 100mA (Note 7)	CNR = 1nF	--	15.6 x V _{OUT}	--	μV _{RMS}
			CNR = 10nF	--	15.6 x V _{OUT}	--	
			CNR = 0.1μF	--	15.1 x V _{OUT}	--	
Over-Temperature Protection							
Over-Temperature Protection Threshold	T _{OTP}	(Note 7)		--	160	--	°C
Over-Temperature Protection Hysteresis	T _{OTP_HYS}	(Note 7)		--	20	--	

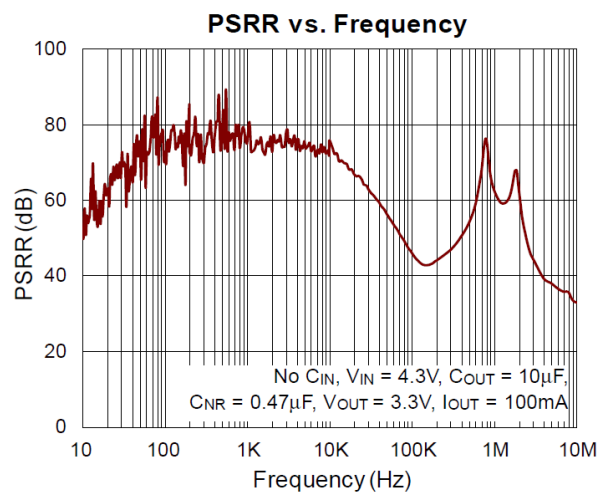
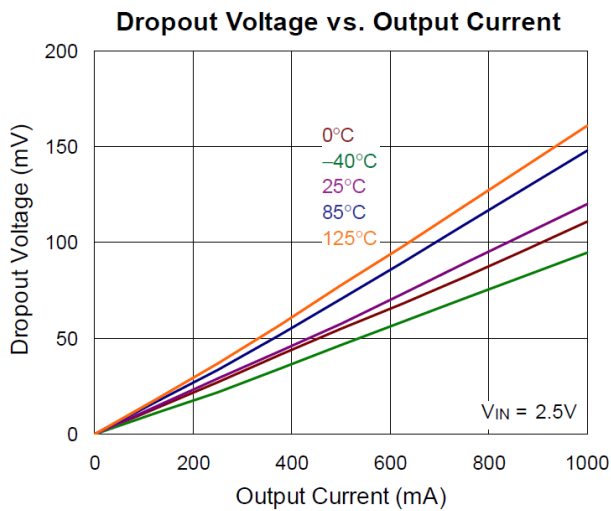
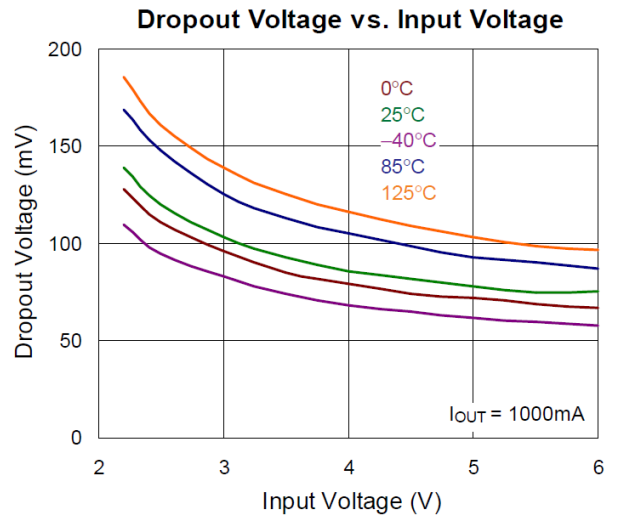
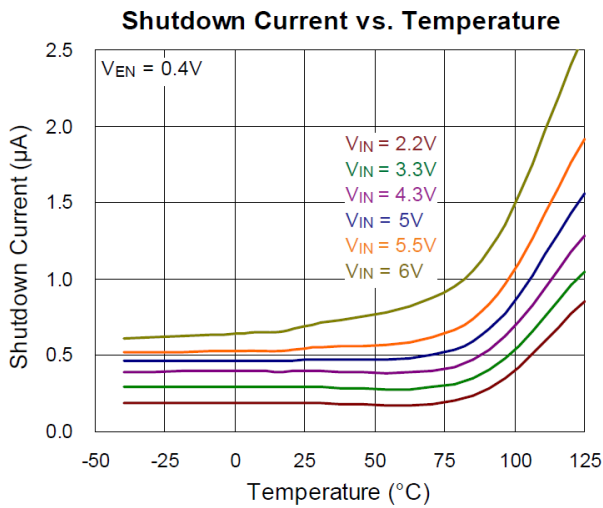
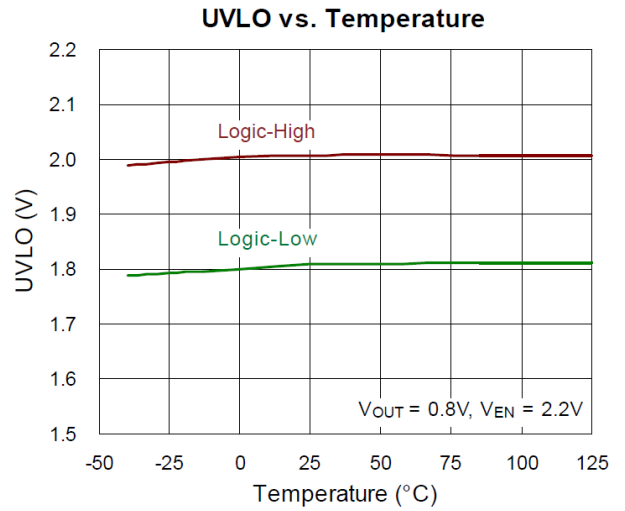
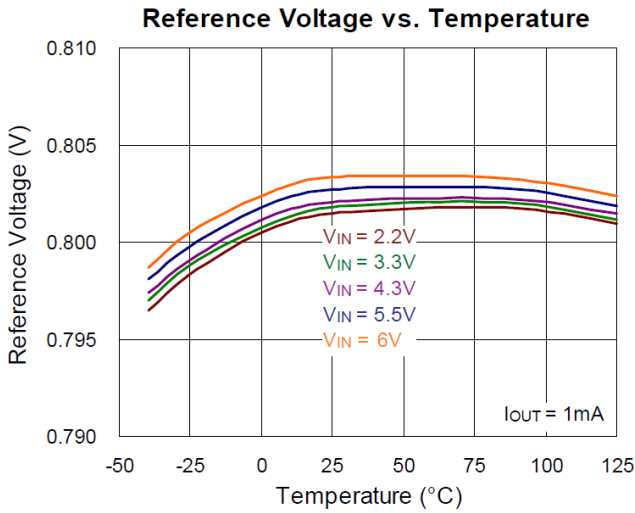
Note 6. The spec doesn't cover the tolerances from external resistors, and which is not tested at condition of V_{OUT} = 0.8V, 4.5V ≤ V_{IN} ≤ 6V, and 750mA ≤ I_{OUT} ≤ 1A since the power dissipation of the device is totally higher than the maximum rating of the package to lead a thermal shutdown issue.

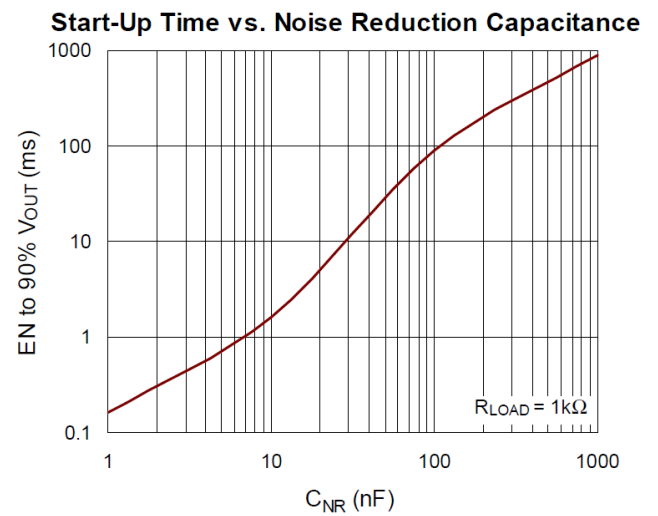
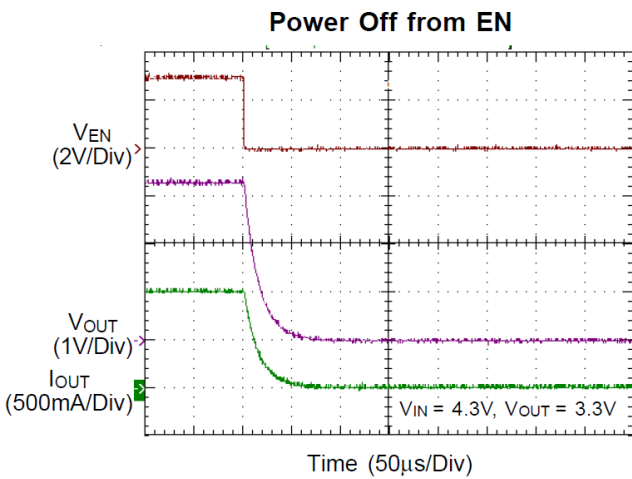
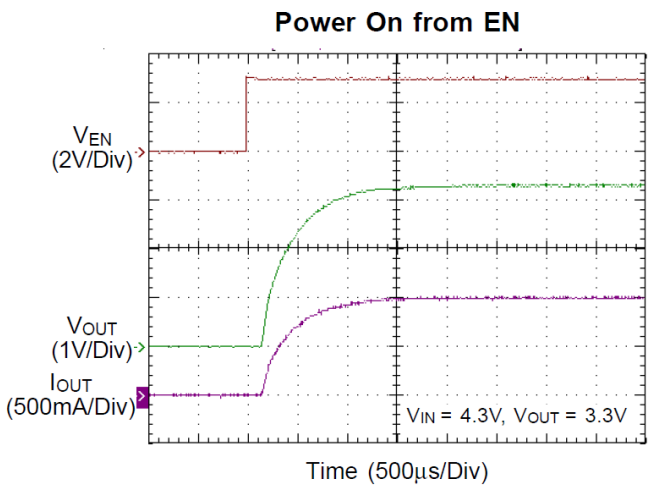
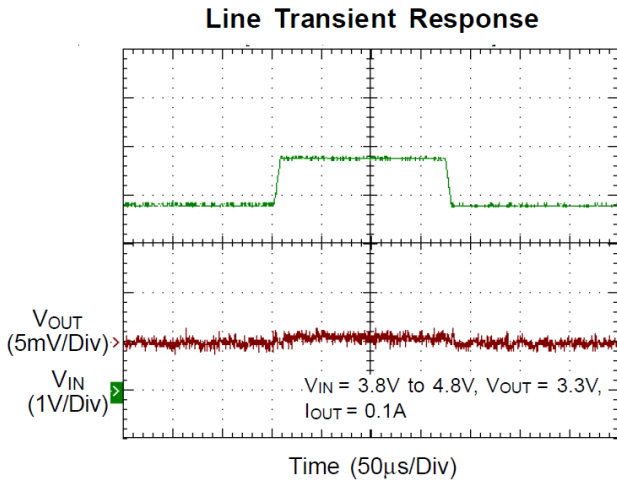
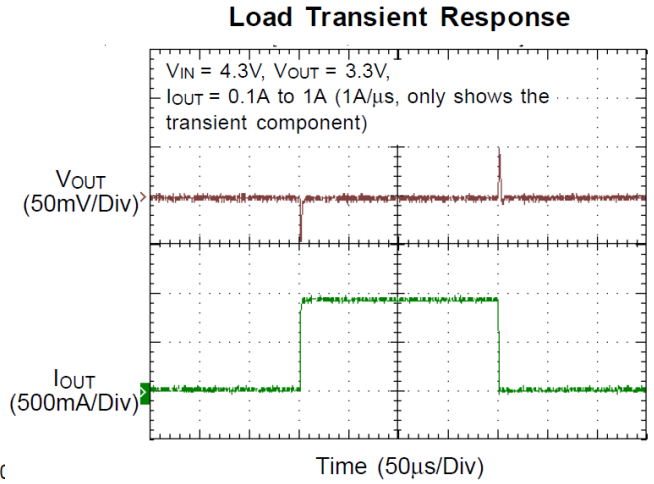
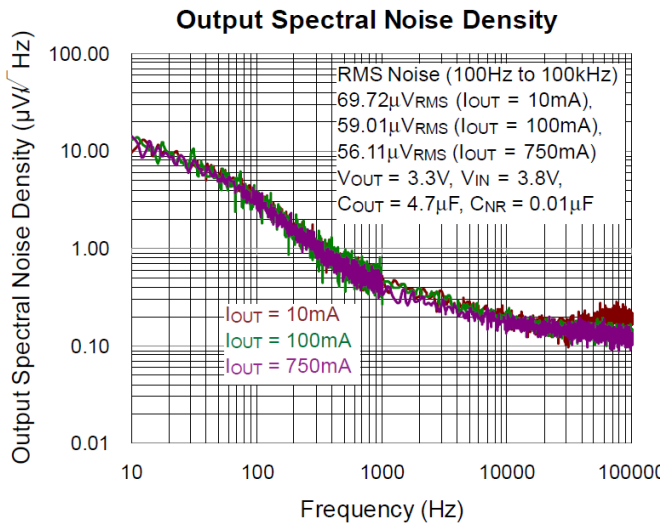
Note 7. Guarantee by design.

14 Typical Application Circuit



15 Typical Operating Characteristics





16 Operation

The RTQ2510 is a low noise, high PSRR LDO which supports very low dropout operation. The operating input range is from 2.2V to 6V, the output voltage is programmable as low as 0.8V, and the output current can be up to 1A. The internal compensation network is well designed to achieve fast transient response with good stability.

In steady-state operation, the feedback voltage is regulated to the reference voltage by the internal regulator. When the feedback voltage signal is less than the reference, the output current passing through the power MOSFET will increase. The additional current is sent to the output until the voltage level of the FB pin returns to the reference.

On the other hand, if the feedback voltage is higher than the reference, the power MOSFET current is decreased. The excess charge at the output can be released by the loading current.

16.1 Start-Up

The RTQ2510 has a quick-start circuit to charge the noise reduction capacitor (C_{NR}). The switch of the quick-start circuit is closed at start up.

To reduce the noise from the bandgap, there is a low-pass (RC) filter consisting of the C_{NR} and the resistance, which is connected with the bandgap, as shown in the Functional Block Diagrams.

At the start-up, the quick-start switch is closed, with only 35kΩ resistance between the bandgap and NR pin. The quick-start switch opens approximately 2ms after the device is enabled, and the resistance between NR and bandgap is about 224kΩ to form a very good low pass filter with great noise reduction performance.

The 35kΩ resistance is used to slow down the reference voltage ramp to avoid inrush current at chip start-up, and the start-up time can be calculated as :

$$t_{SS} (\text{sec}) = 160000 \times C_{NR} (F)$$

It is recommended that the C_{NR} value be larger than 0.01μF to reduce noise, and low-leakage ceramic capacitors are suitable. However, if the C_{NR} value is too large, the start-up time will be extended significantly if the C_{NR} is not fully charged within 2ms and the quick-start switch is opened. The C_{NR} will be charged through a higher resistance of 224kΩ, which will take much longer to complete the start-up process.

16.2 Enable and Shutdown Operation

The RTQ2510 goes into sleep mode when the EN pin is in a logic low condition. In this condition, the pass transistor, error amplifier, and bandgap are all turned off, reducing the supply current to only 2μA (max.). If the shutdown mode is not required, the EN pin can be directly tied to VIN pin to keep the LDO on.

16.3 Current Limit

The RTQ2510 continuously monitors the output current to protect the pass transistor against abnormal operations. When an overload or short circuit is encountered, the current limit circuitry controls the pass transistor's gate voltage to limit the output within the predefined range. Due to the built-in body diode, the pass transistor conducts current when the output voltage exceeds the input voltage. Since the current is not limited, external current protection should be added if the device may work at a reverse voltage state.

16.4 Over-Temperature Protection (OTP)

The RTQ2510 has over-temperature protection. When the device triggers the OTP, the device shuts down until the temperature returns to a normal state.

16.5 Undervoltage Lockout (UVLO)

The RTQ2510 utilizes an undervoltage lockout circuit to keep the output shutdown until the internal circuitry is operating properly. The UVLO circuit has a de-glitch feature so that it typically ignores undershoot transients on the input if they are less than 30 μ s duration.

17 Application Information

Richtek's component specification does not include the following information in the Application Information section. Thereby no warranty is given regarding its validity and accuracy. Customers should take responsibility to verify their own designs and reserve suitable design margin to ensure the functional suitability of their components and systems.

The RTQ2510 is a low voltage, low dropout linear regulator with input voltage from 2.2V to 6V and a fixed output voltage from 0.8V to 5.5V.

17.1 Dropout Voltage

The dropout voltage refers to the voltage difference between the VIN and VOUT pins while operating at a specific output current. The dropout voltage V_{DROP} can also be expressed as the voltage drop across the pass-FET at a specific output current (I_{RATED}) while the pass-FET is fully operating in the ohmic region, and the pass-FET can be characterized as a resistance R_{DS(on)}. Thus, the dropout voltage can be defined as (V_{DROP} = V_{VIN} - V_{VOUT} = R_{DS(on)} × I_{RATED}).

For normal operation, the suggested LDO operating range is (V_{VIN} > V_{VOUT} + V_{DROP}) for good transient response and PSRR ability. Conversely, operating in the ohmic region will severely degrade these performance.

17.2 Output Voltage Setting

For the RTQ2510, the voltage on the FB pin sets the output voltage and is determined by the values of R1 and R2. The values of R1 and R2 can be calculated for any voltage using the formula given in the equation below :

$$V_{OUT} = \frac{(R1 + R2)}{R2} \times 0.8$$

Using lower values for R1 and R2 is recommended to reduce the noise injected from the FB pin. Note that R1 is connected from V_{OUT} pin to FB pin, and R2 is connected from FB to GND.

17.3 Chip Enable Operation

The EN pin is the chip enable input. Pulling the EN pin low (<0.4V) will shut down the device. During shutdown mode, the RTQ2510 quiescent current drops to lower than 2μA. Driving the EN pin high (>1.2V, <6V) will turn on the device again. For external timing control (e.g. RC), the EN pin can also be externally pulled to high by adding a 100kΩ or greater resistor from the VIN pin.

17.4 Current Limit

The RTQ2510 continuously monitors the output current to protect the pass transistor against abnormal operations. When an overload or short circuit is encountered, the current limit circuitry controls the pass transistor's gate voltage to limit the output within the predefined range. Due to the built-in body diode, the pass transistor conducts current when the output voltage exceeds the input voltage. Since the current is not limited, external current protection should be added if the device may operate at a reverse voltage state.

17.5 C_{IN} and C_{OUT} Selection

Like any low dropout regulator, the external capacitors of the RTQ2510 must be carefully selected for regulator stability and performance. Using a capacitor of at least 4.7μF is suitable. The input capacitor must be located at a distance of no more than 0.5 inch from the input pin of the chip. Any good quality ceramic capacitor can be used. However, a capacitor with larger value and lower ESR (Equivalent Series Resistance) is recommended since it

will provide better PSRR and line transient response.

The RTQ2510 is designed specifically to work with low ESR ceramic output capacitor for space saving and performance consideration. Using a ceramic capacitor with capacitance of at least 4.7µF on the RTQ2510 output ensures stability.

17.6 Output Noise

Generally speaking, the dominant noise source is from the internal bandgap for most LDOs. With the noise reduction capacitor connected to the NR pin of the RTQ2510, the noise component contributed from the bandgap will not be significant. Instead, the most significant noise source comes from the output resistor divider and the error amplifier input. For general noise reduction in applications, it is recommended to use a 0.01µF noise-reduction capacitor (CNR).

17.7 Thermal Considerations

Thermal protection limits power dissipation in the RTQ2510. When the operating junction temperature exceeds 160°C, the OTP circuit initiates the thermal shutdown function and turns off the pass element. The pass element turns on again after the junction temperature decreases by 20°C.

The RTQ2510 output voltage will be close to zero when an output short circuit occurs, as shown in [Figure 1](#). This can reduce the chip temperature and provide maximum safety to end users when an output short circuit occurs.

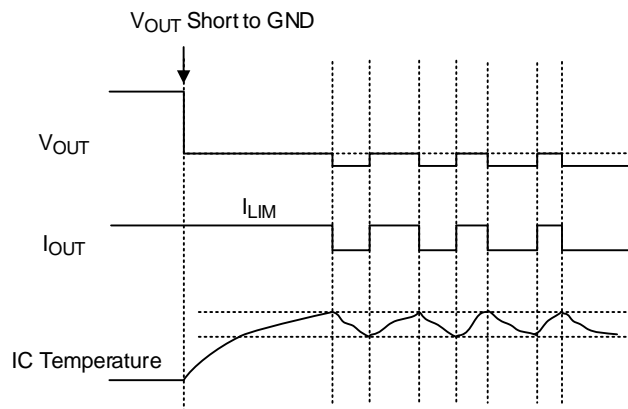


Figure 1. Short-Circuit Protection when Output Short-Circuit Occurs

The junction temperature should never exceed the absolute maximum junction temperature $T_{J(MAX)}$, listed under Absolute Maximum Ratings, to avoid permanent damage to the device. The maximum allowable power dissipation depends on the thermal resistance of the IC package, the PCB layout, the rate of surrounding airflow, and the difference between the junction and ambient temperatures. The maximum power dissipation can be calculated using the following formula :

$$P_{D(MAX)} = (T_{J(MAX)} - T_A) / \theta_{JA}$$

where $T_{J(MAX)}$ is the maximum junction temperature, T_A is the ambient temperature, and θ_{JA} is the junction-to-ambient thermal resistance.

For continuous operation, the maximum operating junction temperature indicated under Recommended Operating Conditions is 125°C. The junction-to-ambient thermal resistance, θ_{JA} , is highly package dependent. For a VDFN-8L 3x3 package, the thermal resistance, θ_{JA} , is 45.06°C/W on a standard JEDEC 51-7 high effective-thermal-conductivity four-layer test board. The maximum power dissipation at $T_A = 25^\circ\text{C}$ can be calculated as below :

$$P_{D(MAX)} = (125^\circ\text{C} - 25^\circ\text{C}) / (45.06^\circ\text{C/W}) = 2.22\text{W for a VDFN-8L 3x3 package.}$$

The maximum power dissipation depends on the operating ambient temperature for the fixed $T_{J(MAX)}$ and the thermal resistance, θ_{JA} . The derating curve in [Figure 2](#) allows the designer to see the effect of rising ambient temperature on the maximum power dissipation.

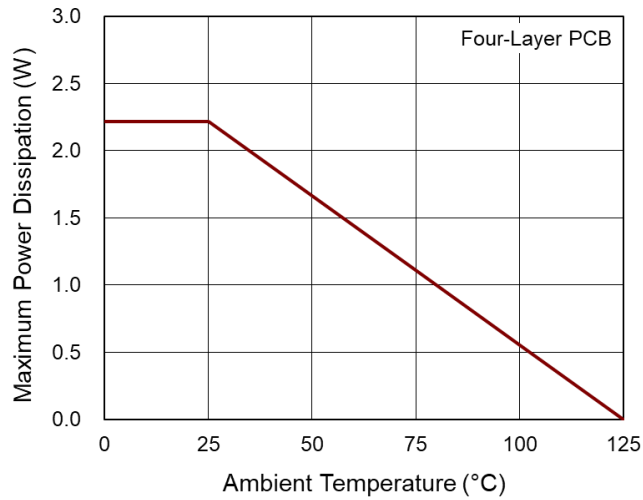


Figure 2. Derating Curve of Maximum Power Dissipation

17.8 Layout Considerations

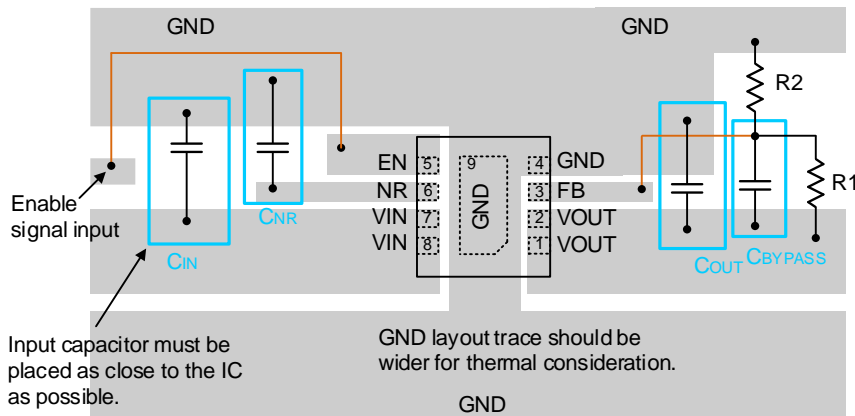
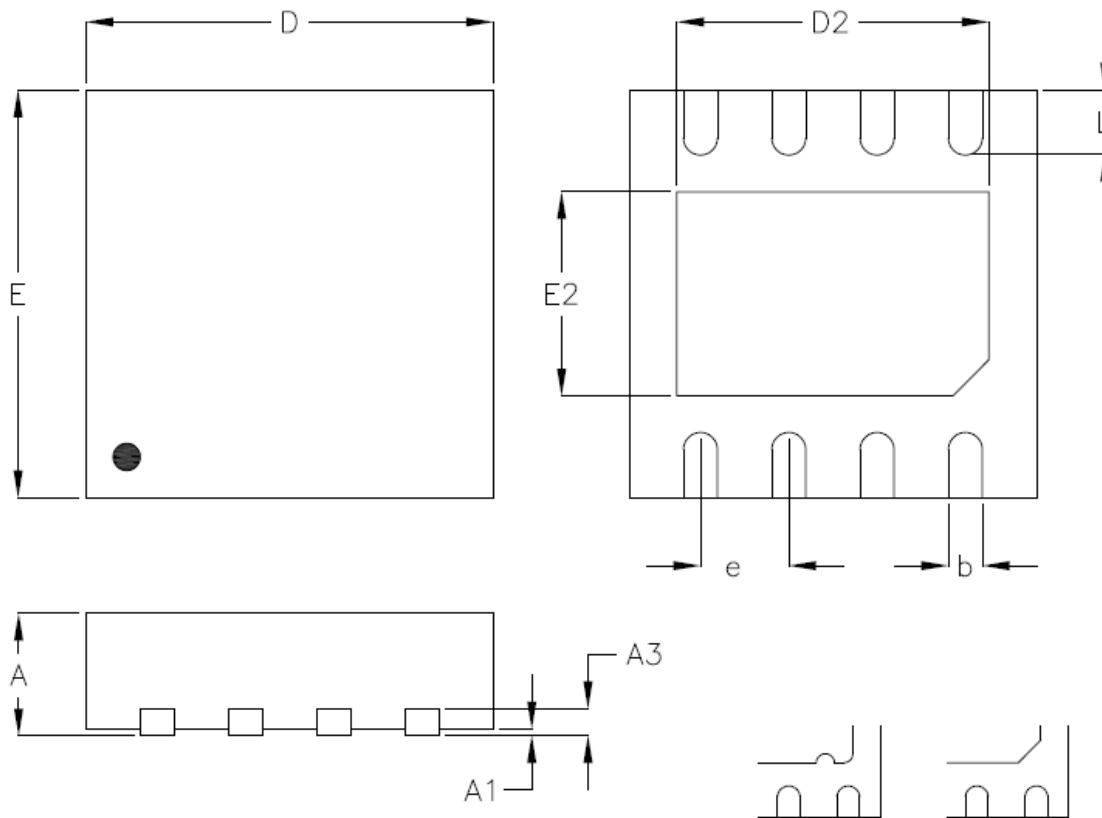


Figure 3. PCB Layout Guide

18 Outline Dimension



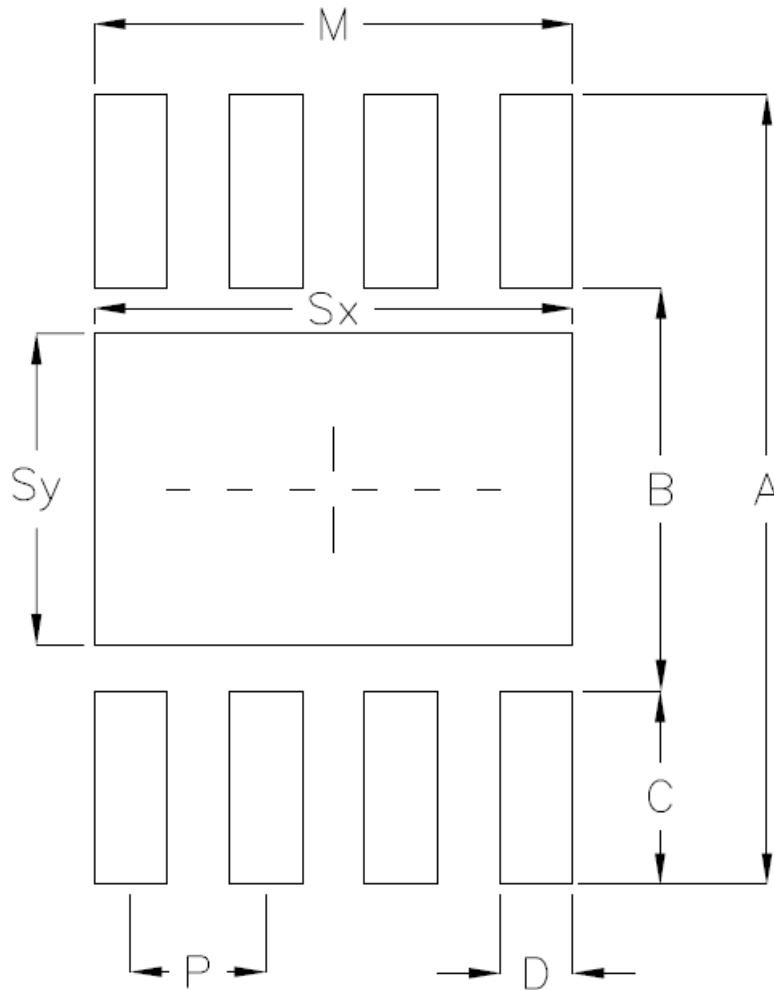
DETAILA
Pin #1 ID and Tie Bar Mark Options

Note : The configuration of the Pin #1 identifier is optional, but must be located within the zone indicated.

Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.700	0.900	0.027	0.035
A1	0.000	0.050	0.000	0.002
A3	0.175	0.250	0.007	0.010
b	0.200	0.300	0.008	0.012
D	2.950	3.050	0.116	0.120
D2	2.100	2.350	0.083	0.093
E	2.950	3.050	0.116	0.120
E2	1.350	1.600	0.053	0.063
e	0.650		0.026	
L	0.425	0.525	0.017	0.021

V-Type 8L DFN 3x3 Package

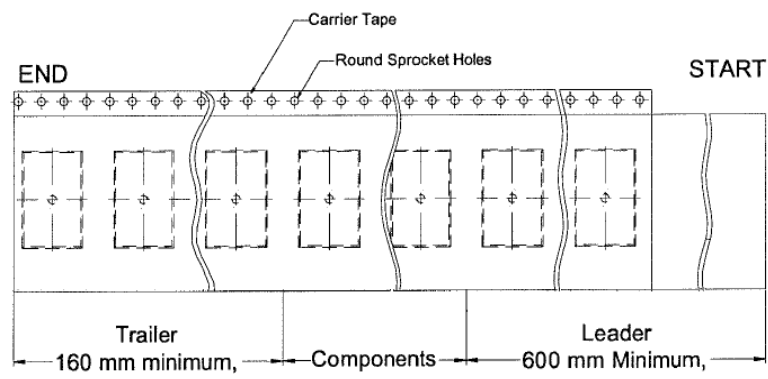
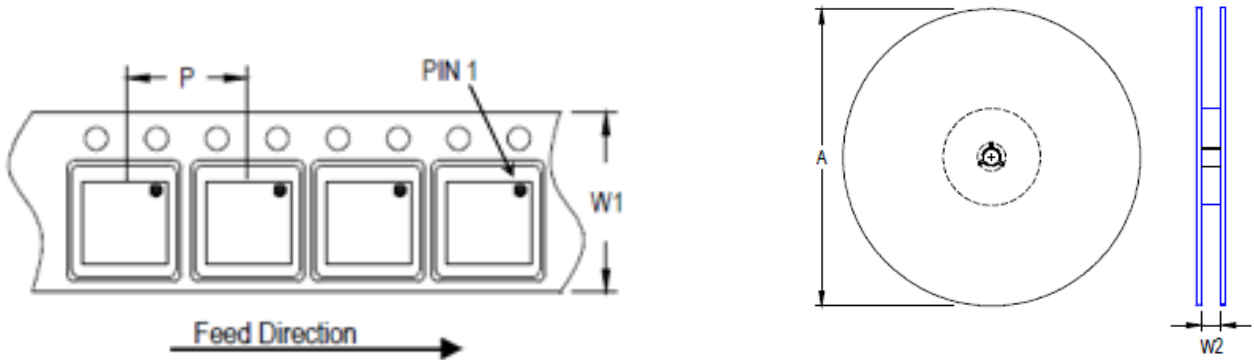
19 Footprint Information



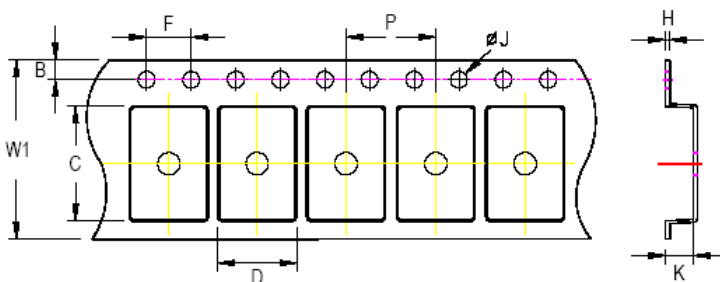
Package	Number of Pin	Footprint Dimension (mm)								Tolerance
		P	A	B	C	D	Sx	Sy	M	
VW/U/XDFN3*3-8	8	0.65	3.80	1.94	0.93	0.35	2.30	1.50	2.30	±0.05

20 Packing Information

20.1 Tape and Reel Data









Package Type	Tape Size (W1) (mm)	Pocket Pitch (P) (mm)	Reel Size (A)		Units per Reel	Trailer (mm)	Leader (mm)	Reel Width (W2) Min./Max. (mm)
			(mm)	(in)				
QFN/DFN 3x3	12	8	180	7	1,500	160	600	12.4/14.4



C, D, and K are determined by component size.
The clearance between the components and the cavity is as follows:
- For 12mm carrier tape: 0.5mm max.

Tape Size	W1		P		B		F		ØJ		H
	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Max.	
12mm	12.3mm	7.9mm	8.1mm	1.65mm	1.85mm	3.9mm	4.1mm	1.5mm	1.6mm	0.6mm	

20.2 Tape and Reel Packing

Step	Photo/Description	Step	Photo/Description
1	 <p>Reel 7"</p>	4	 <p>3 reels per inner box Box A</p>
2	 <p>HIC & Desiccant (1 Unit) inside</p>	5	 <p>12 inner boxes per outer box</p>
3	 <p>Caution label is on backside of Al bag</p>	6	 <p>Outer box Carton A</p>

Container Package	Reel		Box				Carton			
	Size	Units	Item	Size(cm)	Reels	Units	Item	Size(cm)	Boxes	Unit
QFN/DFN 3x3	7"	1,500	Box A	18.3*18.3*8.0	3	4,500	Carton A	38.3*27.2*40.0	12	54,000
			Box E	18.6*18.6*3.5	1	1,500	For Combined or Partial Reel.			

20.3 Packing Material Anti-ESD Property

Surface Resistance	Aluminum Bag	Reel	Cover tape	Carrier tape	Tube	Protection Band
Ω/cm^2	10^4 to 10^{11}	10^4 to 10^{11}	10^4 to 10^{11}	10^4 to 10^{11}	10^4 to 10^{11}	10^4 to 10^{11}

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21 Datasheet Revision History

Version	Date	Description	Item
03	2024/3/14	Modify	Ordering Information on P1 Absolute Maximum Ratings on P5 Recommended Operating Conditions on P5 Thermal Information on P5 Note 4, Note 5 on P5 Application Information on P14, 5